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November 2018

FQB8P10

P-Channel QFET[®] MOSFET

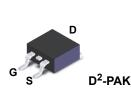
-100 V, -8.0 A, 530 mΩ

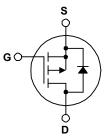
Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- -8.0 A, -100 V, $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ = 530 m Ω (Max.) @ V_{GS} = -10 V, I_D = -4.0 A
- Low Gate Charge (Typ. 12 nC)
- Low Crss (Typ. 30 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





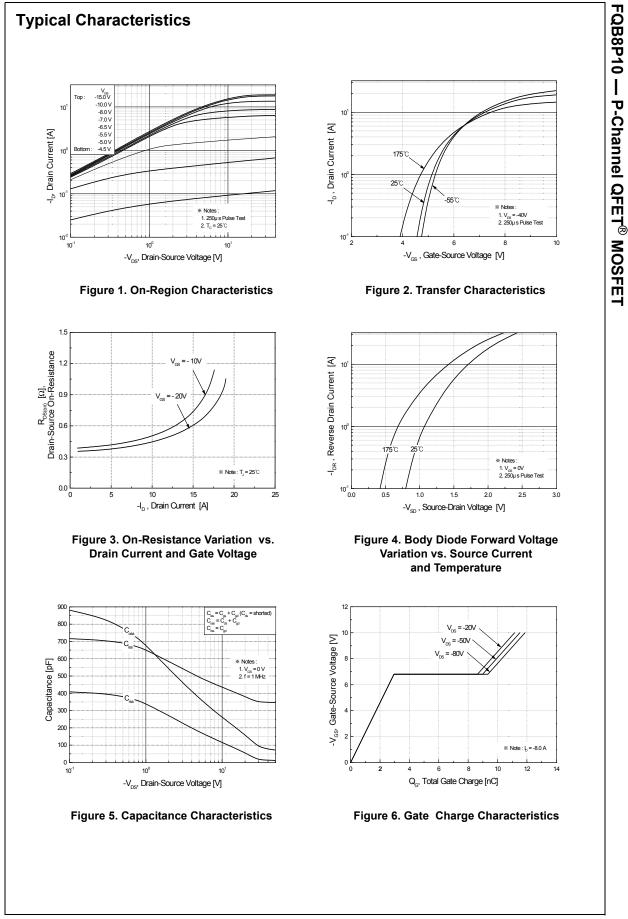
Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

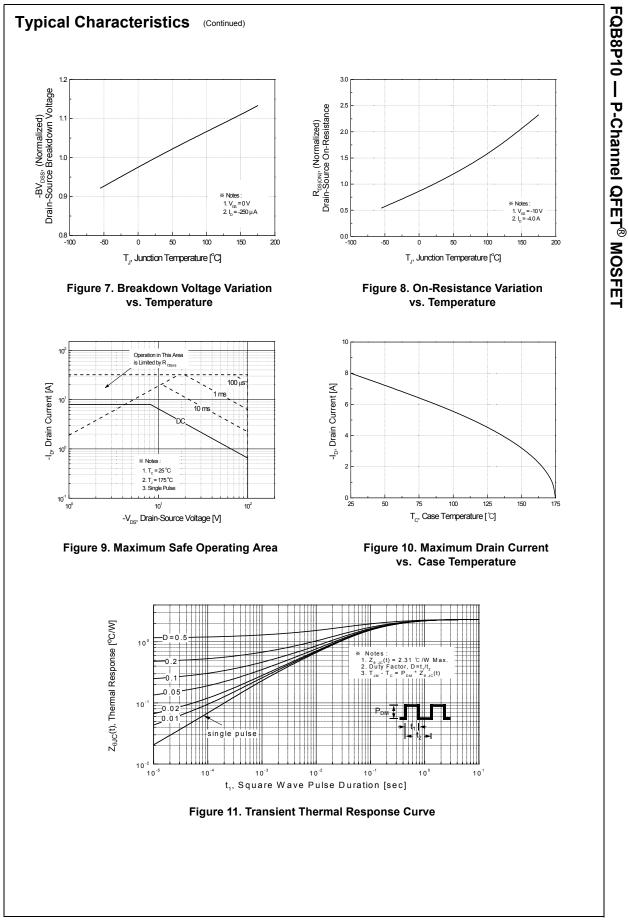
Symbol	Parameter		FQB8P10TM	Unit
V _{DSS}	Drain-Source Voltage		-100	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		-8.0	A
	- Continuous (T _C = 100°C)		-5.7	A
I _{DM}	Drain Current - Pulsed	(Note 1)	-32	A
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	150	mJ
I _{AR}	Avalanche Current	(Note 1)	-8.0	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	6.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-6.0	V/ns
P _D	Power Dissipation $(T_A = 25^{\circ}C)^{*}$		3.75	W
	Power Dissipation ($T_C = 25^{\circ}C$)		65	W
	- Derate above 25°C		0.43	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C

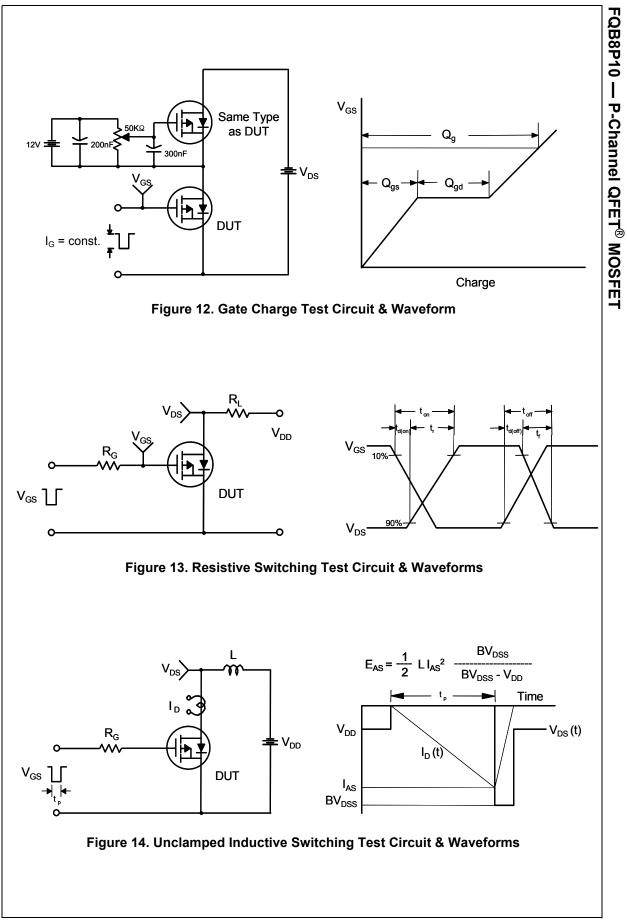
Thermal Characteristics

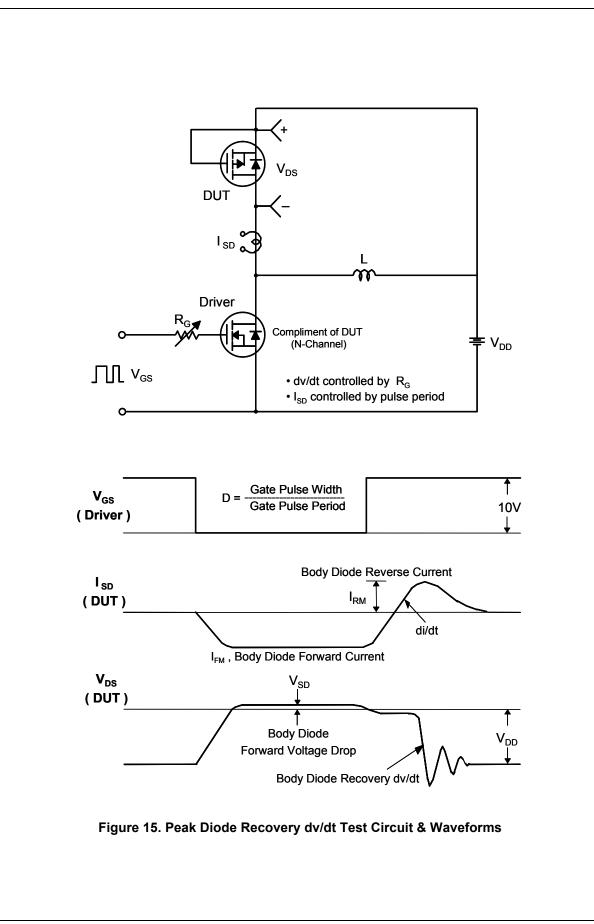
Symbol	Parameter	FQB8P10TM	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	2.31		
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W	
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40		

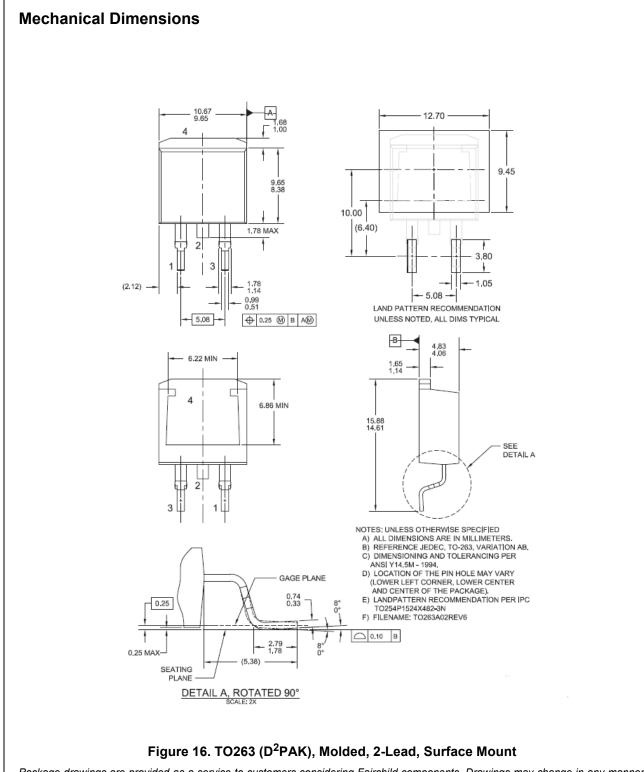
•		Packa	ackagePacking MethodReelD2-PAKTape and Reel330		Size	Tape Width 24 mm		Quantity 800 units		
		D ² -P			mm					
lectri	cal Cha	racteristics	T _C = 25°C	unless otl	herwise noted.					
Symbol		Parameter			Test Conditions		Min.	Тур.	Max.	Unit
Off Cha	racterist	ics								
BV _{DSS}		Irce Breakdown Voltag	ge	V _{GS} =	0 V, I _D = -250 μA		-100			V
ΔBV _{DSS} /ΔT _J	Breakdow Coefficien	wn Voltage Temperature ent		I_D = -250 μ A, Referenced to 25°C				-0.1		V/°C
DSS	Zero Cate	Voltage Drain Curren	, +	-	-100 V, V _{GS} = 0 V				-1	μA
	Zero Gate Voltage Drain Current		it i	V _{DS} = -80 V, T _C = 150°C				-10	μA	
GSSF		y Leakage Current, Fo			-30 V, V _{DS} = 0 V				-100	nA
GSSR	Gate-Bod	y Leakage Current, Re	everse	V _{GS} =	30 V, V _{DS} = 0 V				100	nA
On Cha	racterist	ics								
V _{GS(th)}	Gate Thre	shold Voltage		V _{DS} =	V _{GS} , I _D = -250 μA		-2.0		-4.0	V
R _{DS(on)}	Static Dra On-Resist	Drain-Source esistance		00	-10 V, I _D = -4.0 A			0.41	0.53	Ω
9 _{FS}	Forward 1	Forward Transconductance			V _{DS} = -40 V, I _D = -4.0 A			4.3	-	S
C _{iss} C _{oss}	Input Cap Output Ca	apacitance		V _{DS} = f = 1.0	-25 V, V _{GS} = 0 V, MHz			360 120	470 155	pF pF
C _{rss}	Reverse	Fransfer Capacitance						30	40	pF
Switchi	ing Chara	acteristics								
d(on)	-	Delay Time		V_{DD} = -50 V, I _D = -8.0 A, R _G = 25 Ω				11	30	ns
r	Turn-On F	Rise Time						110	230	ns
d(off)	Turn-Off	Delay Time					20	50	ns	
f	Turn-Off F	all Time				(Note 4)		35	80	ns
כ ^d	Total Gate	e Charge		V _{DS} =	-80 V, I _D = -8.0 A,			12	15	nC
ସ୍ _{gs}	Gate-Sou	rce Charge		$V_{GS} =$				3.0	-	nC
Q _{gd}	Gate-Drai	n Charge				(Note 4)		6.4		nC
			4	al 84 -	dan					
		ode Characteris			•				0 0	۸
S		Pulsed Drain-Source							-8.0 -32	A
sм √ _{SD}		Irce Diode Forward Vo			0 V, I _S = -8.0 A				-32 -4.0	A V
		Recovery Time	maye		$0 \text{ V}, \text{ I}_{\text{S}} = -8.0 \text{ A},$			98	-4.0	-
t _{rr} Q _{rr}		Recovery Charge			t = 100 A/μs			90 0.35		ns μC
~m	ILEVEISE F	Covery Charge		ы _г , а				0.55		μΟ
L = 3.5 mH,	I _{AS} = -8.0 A, V _I	dth limited by maximum juncti _{DD} = -25 V, R _G = 25 Ω, startin ıs , V _{DD} ≤ BV _{DSS} starting T _{.I}	ig T _J = 25°C							











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FQB8P10 ---

P-Channel QFET[®] MOSFET



Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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